

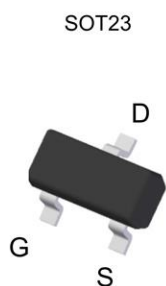
General Features

- $V_{DS} = 30V, I_D = 5.8A$
- $R_{DS(ON)} < 59m\Omega @ V_{GS}=2.5V$
- $R_{DS(ON)} < 45m\Omega @ V_{GS}=4.5V$
- $R_{DS(ON)} < 41m\Omega @ V_{GS}=10V$

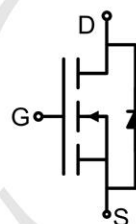
Application

- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable
- Logic Level Shift

Package and Pin Configuration



Circuit diagram



Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current-Continuous	I_D	5.8	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	30	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	89	$^\circ C/W$
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.7	0.9	1.4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =2.5V, I _D =4A	-	45	59	mΩ
		V _{GS} =4.5V, I _D =5A	-	31	45	mΩ
		V _{GS} =10V, I _D =5.8A	-	28	41	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =5A	10	-	-	S
Dynamic Characteristics ^(Note4)						
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	820	-	PF
Output Capacitance	C _{oss}		-	99	-	PF
Reverse Transfer Capacitance	C _{rss}		-	77	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =2.7Ω V _{GS} =10V, R _{GEN} =3Ω	-	3.3	-	nS
Turn-on Rise Time	t _r		-	4.8	-	nS
Turn-Off Delay Time	t _{d(off)}		-	26	-	nS
Turn-Off Fall Time	t _f		-	4	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =5.8A, V _{GS} =4.5V	-	9.5	-	nC
Gate-Source Charge	Q _{gs}		-	1.5	-	nC
Gate-Drain Charge	Q _{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V, I _S =5.8A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	5.8	A

Typical Electrical and Thermal Characteristics

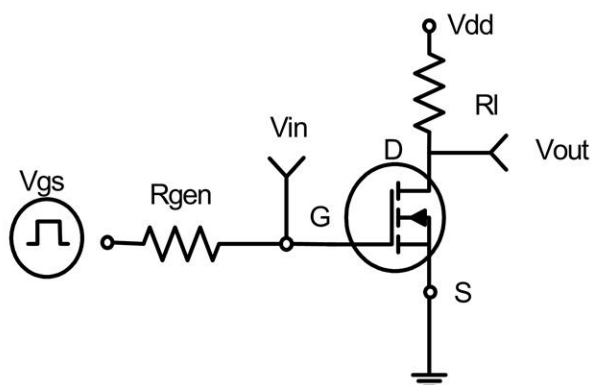


Figure 1: Switching Test Circuit

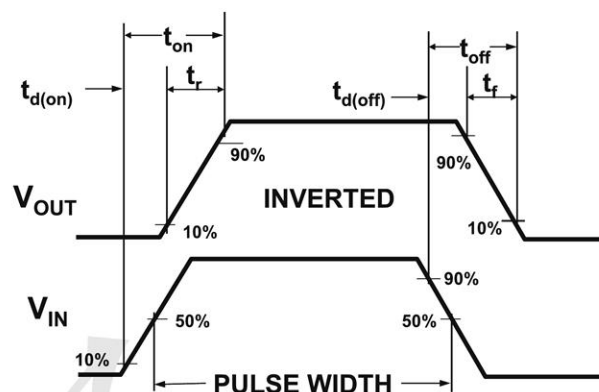


Figure 2: Switching Waveforms

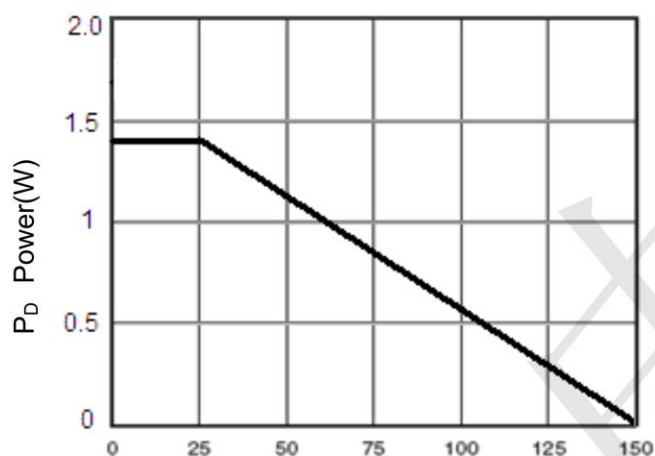


Figure 3 Power Dissipation

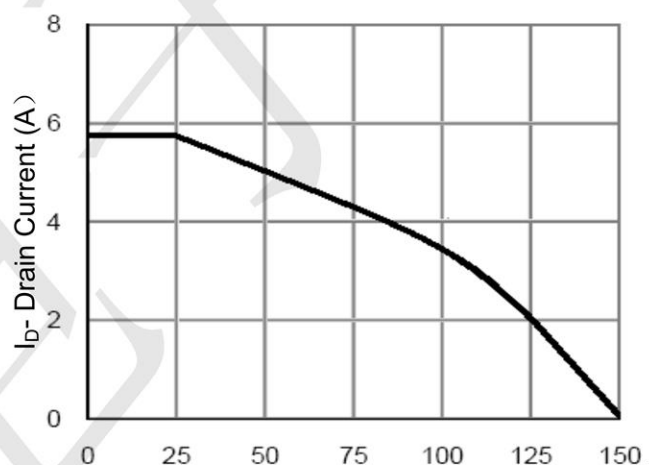


Figure 4 Drain Current

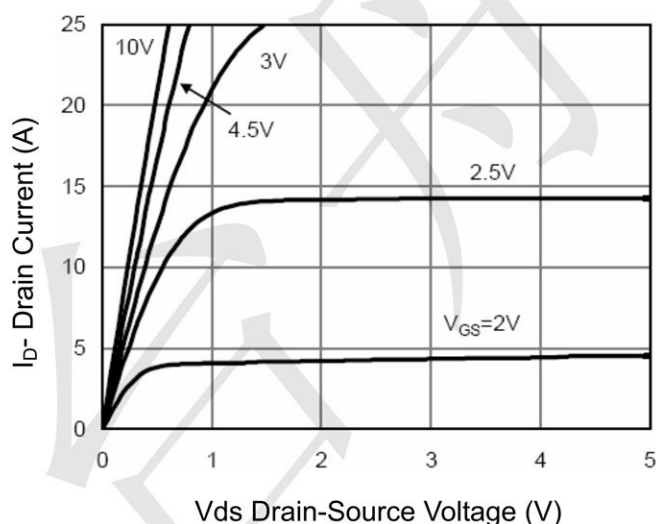


Figure 5 Output Characteristics

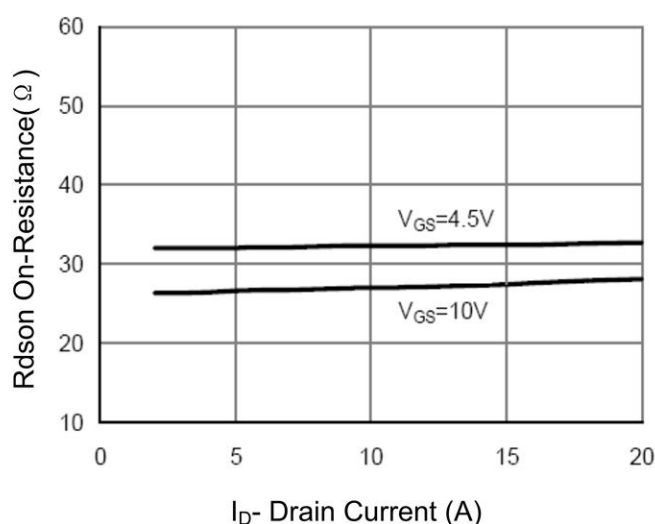


Figure 6 Drain-Source On-Resistance

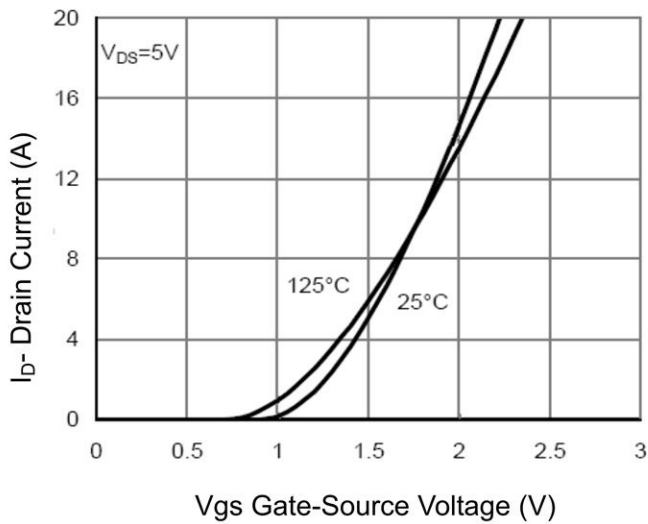
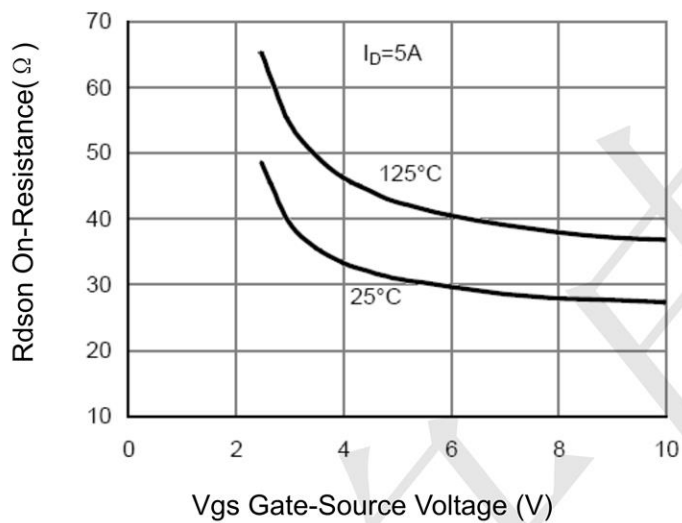


Figure 7 Transfer Characteristics



V_{GS} Gate-Source Voltage (V)

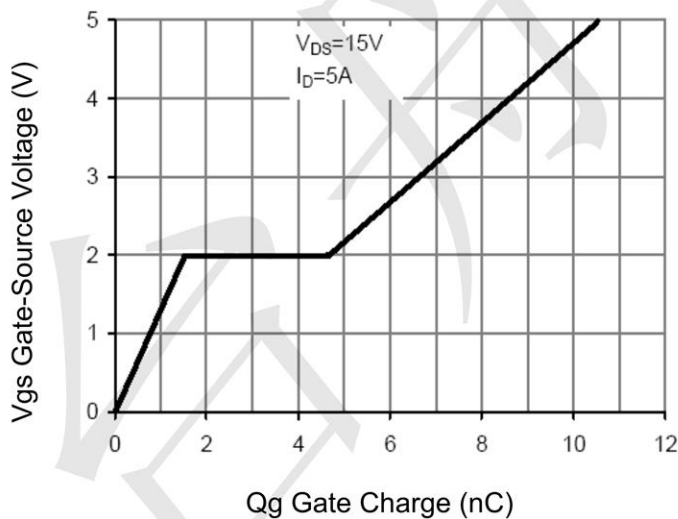


Figure 11 Gate Charge

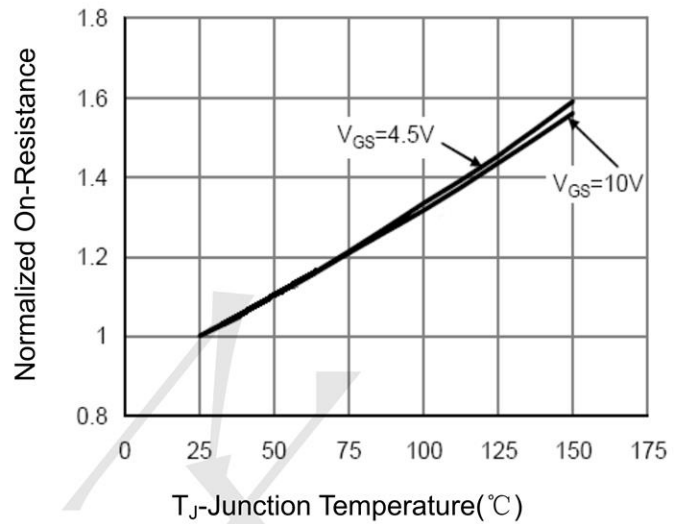
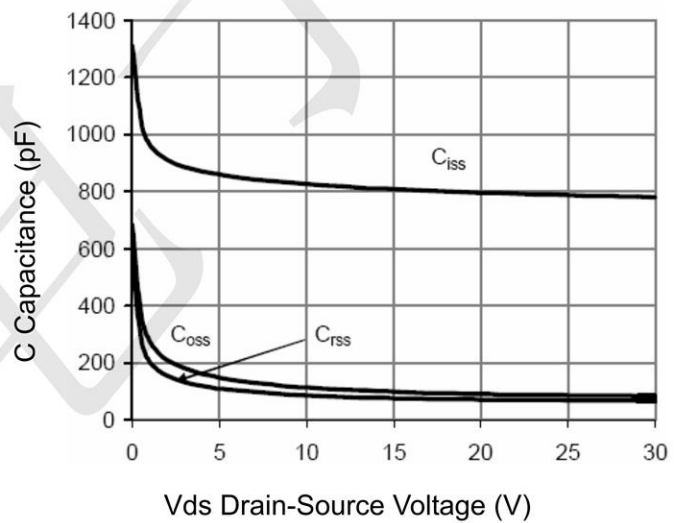


Figure 8 Drain-Source On-Resistance



V_{DS} Drain-Source Voltage (V)

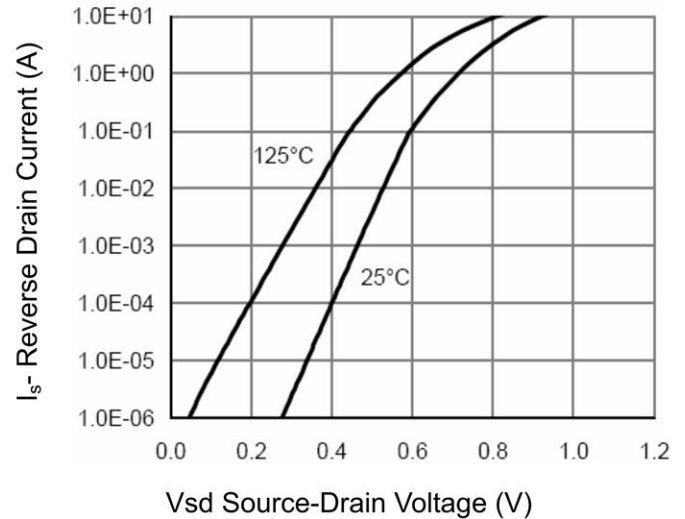


Figure 12 Source- Drain Diode Forward

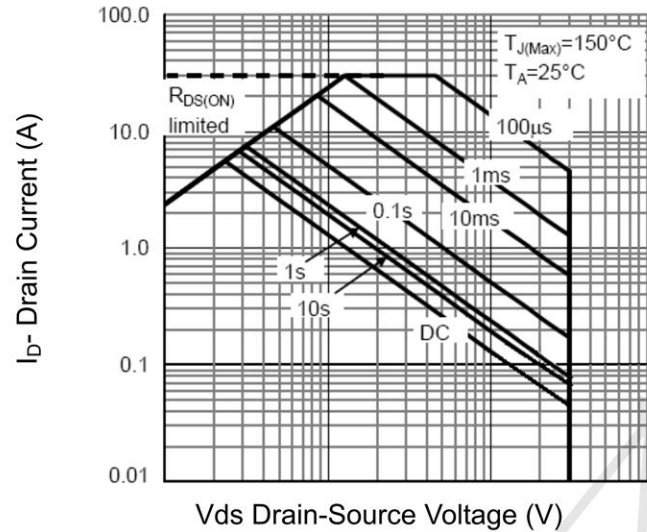


Figure 13 Safe Operation Area

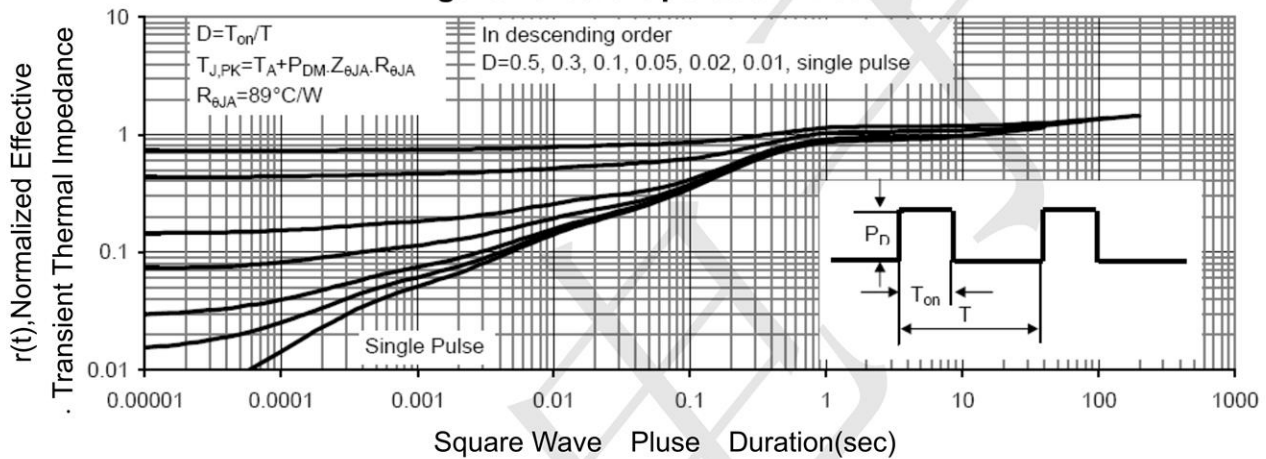
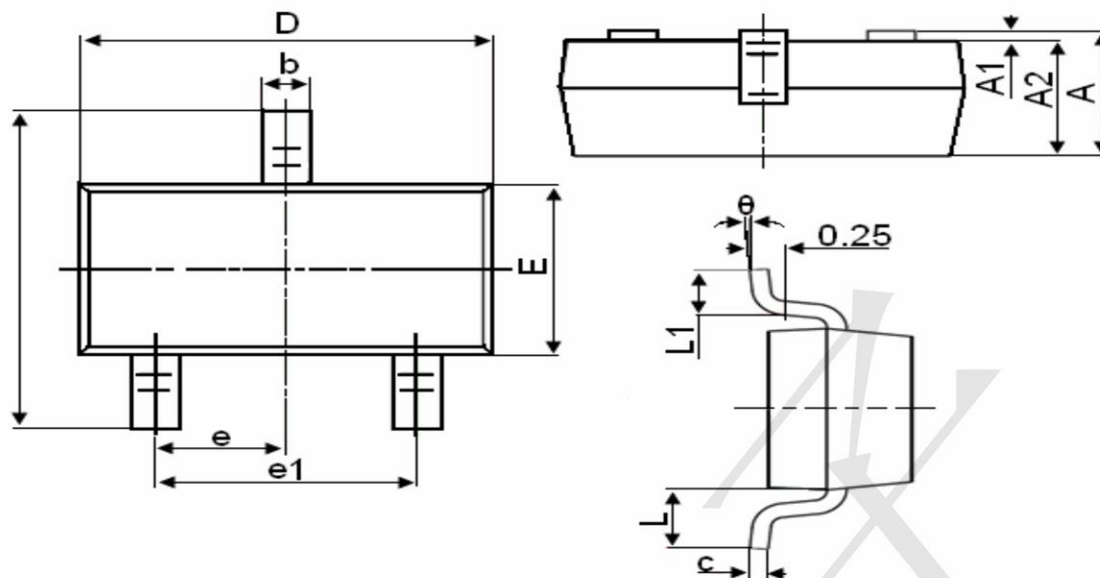


Figure 14 Normalized Maximum Transient Thermal Impedance

Package Outline Dimensions (SOT-23)



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	0.900	1.150
A1	0.000	0.100
A2	0.900	1.050
b	0.300	0.500
c	0.080	0.150
D	2.800	3.000
E	1.200	1.400
E1	2.250	2.550
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.500
θ	0°	8°